

# SG40N01G

40V N-Channel Power MOSFET

	TO-263	D
$V_{\text{DSS}}$ , 40V $R_{\text{DS(ON)}}$ , 2.5m $\Omega$ (max.) @ V_{GS}=10V $I_{D}$ , 149A	GDS	G

Description	Features
The SG40N01G uses advanced Trench technology and designs to provide excellent R <sub>DS(ON)</sub> with low gate charge. This device is suitable for use in PWM, load switching and general purpose applications.	<ul> <li>Low On-Resistance</li> <li>Low Input Capacitance</li> <li>Low Miller Charge</li> <li>Low Input / Output Leakage</li> <li>Pb-free lead plating; RoHS compliant</li> </ul>
	Applications
	<ul> <li>Lithium-Ion Secondary Batteries</li> <li>Load Switch</li> <li>DC-DC converters and Off-line UPS</li> </ul>

#### **Ordering Information**

Ordering Code	RoHS Status	Package	Package Code	Packing	Quantity
SG40N01G	Halogen-Free	TO-263	G	Tape & Reel	800

### Absolute Maximum Ratings (TA=25°C unless otherwise noted)

Parameter		Symbol	Value	Unit
Drain-Source Voltage		V <sub>DS</sub>	40	V
Gate-Source Voltage		Vgs	±20	V
Drain Current-Continuous Note 1	Tc=25°C		149	Α
Drain Current-Continuous Note 1	T <sub>C</sub> =70°C		119	Α
Drain Current-Pulsed Note 1		Ідм	480	Α
Drain Current-Continuous	T <sub>A</sub> =25°C		30	А
Drain Current-Continuous	T <sub>A</sub> =70°C	ID ID	24	А
Avalanche Current		las	63.5	А
Avalanche Energy, L=0.1mH		Eas	201	mJ
	Tc=25°C		83	W
Maximum Dawar Disaination	Tc=70°C	D-	53	W
Maximum Power Dissipation	T <sub>A</sub> =25°C		2	W
	T <sub>A</sub> =70°C		1.3	W
Storage Temperature Range		Tstg	-55 to +150	°C
Operating Junction Temperature Range		TJ	-55 to +150	°C

#### **Thermal Resistance Ratings**

Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Maximum Junction-to-Ambient	Reja	Steady State	-	-	62	°C/W
Maximum Junction-to-Case	R <sub>eJC</sub>	Steady State	-	-	1.5	°C/W



#### Electrical Characteristics (T\_=25°C unless otherwise noted)

OFF CHARACTERISTICS						
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	V <sub>GS</sub> =0V, I <sub>DS</sub> =250µA	40	-	-	V
Zero Gate Voltage Drain Current	IDSS	V <sub>DS</sub> =32V, V <sub>GS</sub> =0V	-	-	1	μA
Gate-Body Leakage	lgss	$V_{GS}=\pm 20V$ , $V_{DS}=0V$	-	-	±100	nA

ON CHARACTERISTICS						
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Gate Threshold Voltage	V <sub>GS(TH)</sub>	Vds=Vgs, Ids=250µA	2	3	4	V
Drain-Source On-State Resistance	Rds(on)	V <sub>GS</sub> =10V, I <sub>DS</sub> =30A	-	-	2.5	mΩ

DYNAMIC CHARACTERISTICS						
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Input Capacitance	Ciss		-	4222	-	
Output Capacitance	Coss	V <sub>DS</sub> =20V, V <sub>GS</sub> =0V, f=1MHz	-	889	-	pF
Reverse Transfer Capacitance	Crss		-	398	-	

SWITCHING CHARACTERISTICS						
Parameter	Symbol	Conditions	Min.	Тур.	Max.	Unit
Turn-On Delay Time	T <sub>d(on)</sub>		-	21	-	
Rise Time	tr	V <sub>DS</sub> =20V, I <sub>DS</sub> =30A, V <sub>GS</sub> =10V,	-	6	-	
Turn-Off Delay Time	T <sub>d(off)</sub>	R <sub>GEN</sub> =3Ω	-	98	-	ns
Fall Time	t <sub>f</sub>		-	17	-	
Total Gate Charge at 10V	Qg		-	78.8	-	
Gate to Source Gate Charge	Qgs	V <sub>DS</sub> =20V, I <sub>DS</sub> =30A, V <sub>GS</sub> =10V	-	23	-	nC
Gate to Drain "Miller" Charge	$Q_{gd}$		-	4.85	-	

DRAIN-SOURCE DIODE CHARACTERISTICS AND MAXIMUM RATINGS							
Parameter Symbol Conditions Min. Typ. Max. Uni						Unit	
Drain-Source Diode Forward Voltage	$V_{\text{SD}}$	V <sub>GS</sub> =0V, I <sub>DS</sub> =30A	-	-	1.3	V	
Body Diode Reverse Recovery Time	trr	1	-	32	-	ns	
Body Diode Reverse Recovery Charge	Qrr	I⊧=30A, dl/dt=100A/µs	-	120	-	nC	

Notes:

1. Pulse Test: Pulse Width  $\leq$  300µs, Duty Cycle  $\leq$  2%.

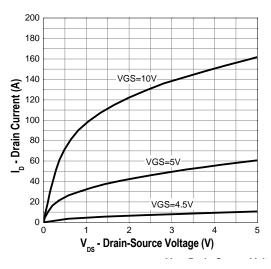
 R<sub>0JA</sub> is the sum of the junction-to-case and case-to-ambient thermal resistance where the case thermal reference is defined as the solder mounting surface of the drain pins. R<sub>0JC</sub> is guaranteed by design while R<sub>0JA</sub> is determined by the user's board design. R<sub>0JA</sub> shown below for single device operation on FR-4 in still air.



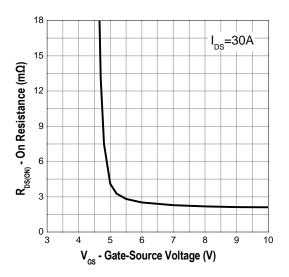
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## **Typical Operating Characteristics**

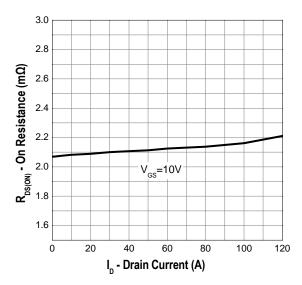
#### **Output Characteristics**



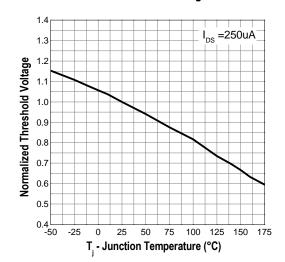
**Gate-Source On Resistance** 



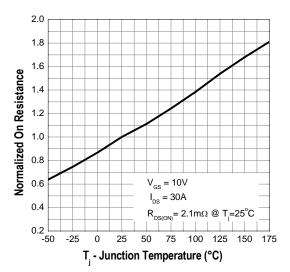
**Drain-Source On Resistance** 



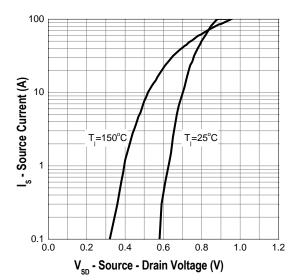
Gate Threshold Voltage



**Drain-Source On Resistance** 



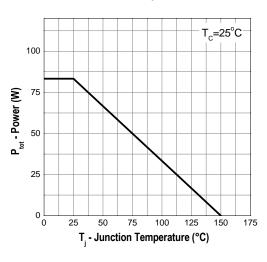




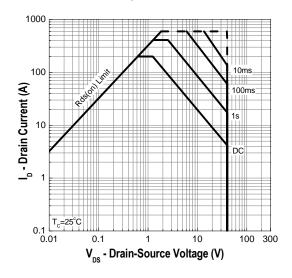


# **Typical Operating Characteristics (Cont.)**

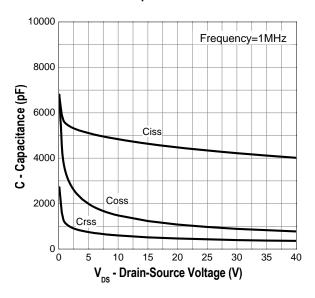
Power Dissipation

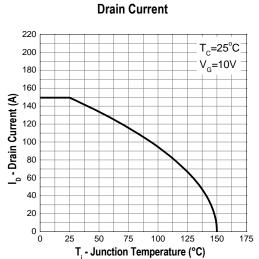


Safe Operation Area

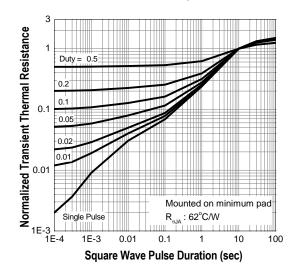


Capacitance

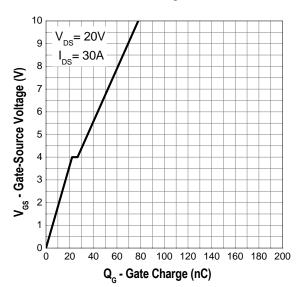




**Transient Thermal Impedance** 



#### **Gate Charge**



# Drain Current

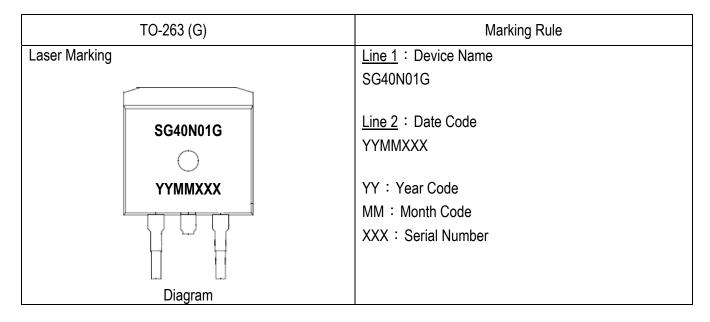
**SG40N01G** 

40V N-Channel Power MOSFET





## **Marking Information**

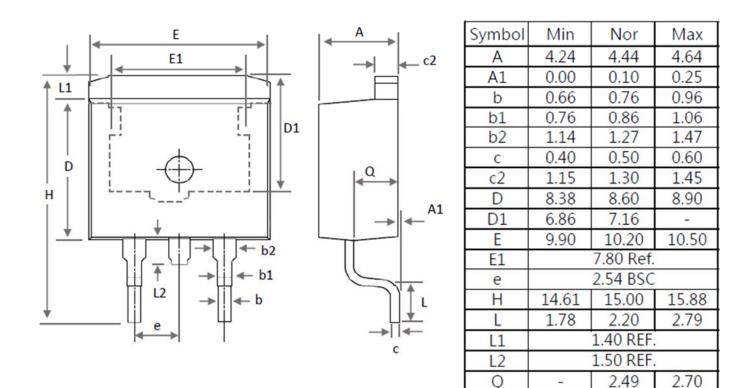




## Package of Dimension

# SG40N01G 40V N-Channel Power MOSFET

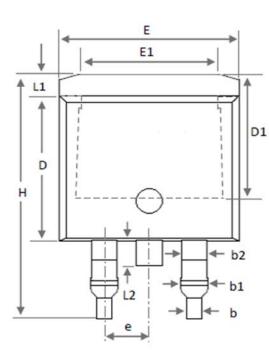
# TO-263S

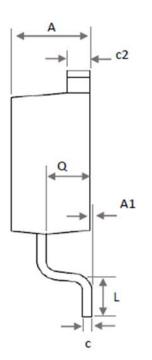




# Package of Dimension

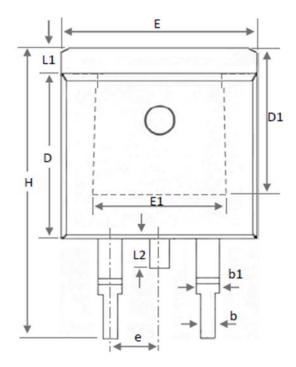
# G-TYPE





Symbol	Min	Nor	Max
A	4.24	4.51	4.77
A1	0.00	0.13	0.25
b	0.70	0.83	0.96
b1	1.17	1.46	1.75
b2	1.20	1.45	1.70
С	0.30	0.45	0.60
c2	1.15	1.29	1.42
D	8.50	8.76	9.02
D1	6.60	7.13	7.65
E	9.86	10.11	10.36
E1	6.89	7.39	7.89
e		2.54 BSC	
Н	14.61	15.25	15.88
L	1.78	2.29	2.79
L1	1.07	1.27	1.47
L2	1.40	1.55	1.70
Q	2.30	2.60	2.89

#### H-TYPE



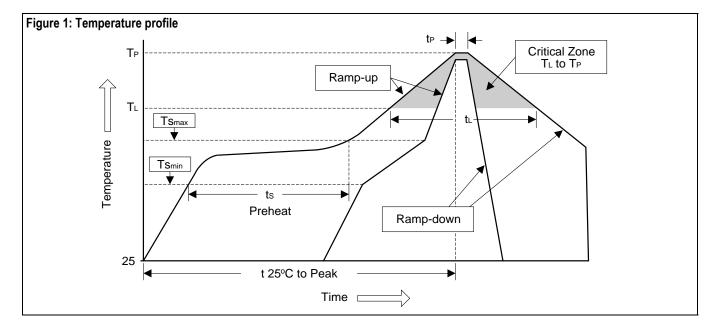
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#### **Soldering Methods for Silicongear's Products**

- 1. Storage environment: Temperature=10°C to 35°C Humidity=65%±15%
- 2. Reflow soldering of surface-mount devices



Profile Feature	Sn-Pb Eutectic Assembly	Pb-Free Assembly
Average ramp-up rate $(T_L \text{ to } T_P)$	<3°C/sec	<3°C/sec
Preheat		
- Temperature Min (Ts <sub>min</sub> )	100°C	150°C
- Temperature Max (Ts <sub>max</sub> )	150°C	200°C
- Time (min to max) (ts)	60 to 120 sec	60 to 180 sec
Tsmax to T∟		
- Ramp-up Rate	<3°C/sec	<3°C/sec
Time maintained above:		
- Temperature (T∟)	183°C	217°C
- Time (t <sub>L</sub> )	60 to 150 sec	60 to 150 sec
Peak Temperature (T <sub>P</sub> )	240°C +0/-5°C	260°C +0/-5°C
Time within 5°C of actual Peak	10 to 30 sec	20 to 40 sec
Temperature (t <sub>P</sub> )		2010-10300
Ramp-down Rate	<6°C/sec	<6°C/sec
Time 25°C to Peak Temperature	<6 minutes	<8 minutes

#### 3. Flow (wave) soldering (solder dipping)

Products	Peak Temperature	Dipping Time
Pb devices.	245°C ±5°C	5sec ±1sec
Pb-Free devices.	260°C +0/-5°C	5sec ±1sec





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